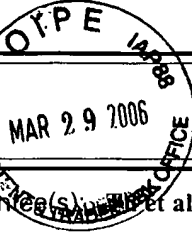10/700,779.   Cofc

TRANSMITTAL LETTER (General - Patent Issued)	Docket No. N1085-90025

Patentee(s): _____ et al.

U.S. Patent No. 6,849,546 B1	Issue Date 2/1/2005

Title: METHOD FOR IMPROVING INTERLEVEL DIELECTRIC GAP FILLING OVER SEMICONDUCTOR STRUCTURES HAVING HIGH ASPECT RATIOS

COMMISSIONER FOR PATENTS:

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Certificate of Correction

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P17A/REV04

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,849,546 *B1*

DATED : 2/1/2005

INVENTOR(S) : Tu et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Claim 3, column 5, line 28, delete "devises" and insert --devices--.
Claim 4, column 5, line 29, delete the first "a" and insert --are--.
Claim 13, column 5, line 63, delete "gas" and insert --gaps--.
Claim 23, column 6, line 48, delete "silicion" and insert --silicon--.

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PATENT NO. 6,849,546

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